

	SINGLE CRYSTALLINE SILICON TFT	MONODOMAIN TFT
GRAIN BOUNDARY	NO	NO
CONCENTRATION OF HYDROGEN (cm ⁻³)	detection limit	1 x 10 ¹⁵ - 1 x 10 ²⁰
ESR (cm ⁻³)	detection limit	1 x 10 ¹⁵ - 1 x 10 ¹⁷
CRYSTALLINITY	YES	YES
MOBILITY ($\frac{\text{cm}^2}{\text{Vs}}$) ($\frac{\text{Vs}}{\text{cm}^2}$)	P-channel: 300-500 N-channel: 800-1200	P-channel: 200-400 N-channel: 500-1000
S VALUE	0.01 - 0.1	0.03 - 0.3
FORM	formed into single crystalline silicon wafer	semiconductor thin film formed on insulating substrate such as glass (strain point of 550- 750 °C) is used.
PROCESS TEMPERATURE (°C)	800-1100, typically 900-1000	450-700 typically 500-650

FIG. 5